

**Study of characteristics of semiconductor GaAs nanoparticles prepared by
laser ablation method**

Abstract:

Gallium arsenide GaAs nanoparticles have been prepared in water using Laser ablation method, the optical properties , energy gap of the colloidal solution have been investigated using UV-Visible spectrometer, the absorption peaks were observed between 200 and 300 nm wavelength and the energy gap was calculated of about 1.86eV. Zeta potential value was about -22.18mv which gives the impression of acceptable stability of the colloidal solution.